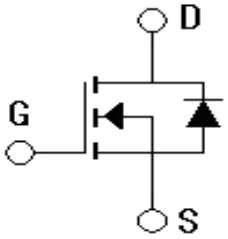
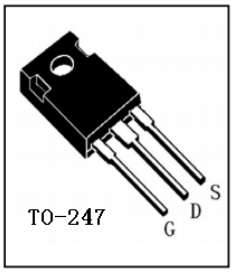
PHJCS50N20T

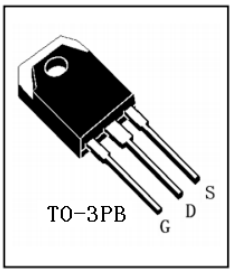
主要参数 MAIN CHARACTERISTICS

I_D	50A
V_{DSS}	200 V
Rdson-max （@Vgs=10V）	50mΩ
Qg-typ	90nC

封装 **Package**







用途

- 高频开关电源
- 电子镇流器
- UPS 电源

APPLICATIONS

- High frequency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- UPS

产品特性

- 低栅极电荷
- 低 C_{rss}
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Low C_{rss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS50N20WT-GE-B	JCS50N20WT-GE-BR	N/A	N/A	JCS50N20WT	TO-247
JCS50N20ABT-GD-B	JCS50N20ABT-GD-BR	N/A	N/A	JCS50N20ABT	TO-3PB

绝对最大额定值 **ABSOLUTE RATINGS** (Tc=25℃)

项　　目 **Parameter**	符　号 **Symbol**	数　值 **Value** JCS50N20WT/ABT	单　位 **Unit**
最高漏极－源极直流电压 Drain-Source Voltage	V_{DSS}	200	V
连续漏极电流 Drain Current　-continuous	I_D　T=25℃	50	A
	T=100℃	31	A
最大脉冲漏极电流(注 1) Drain Current – pulse（note 1）	I_{DM}	200	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	±30	V
单脉冲雪崩能量(注 2) Single Pulsed Avalanche Energy（note 2）	E_{AS}	1000	mJ
雪崩电流(注 1) Avalanche Current（note 1）	I_{AR}	50	A
重复雪崩能量（注 1） Repetitive Avalanche Energy（note 1）	E_{AR}	27.7	mJ
二极管反向恢复最大电压变化速率(注 3) Peak Diode Recovery dv/dt（note 3）	dv/dt	5.4	V/ns
耗散功率 Power Dissipation	P_D T_C=25℃	277	W
	-Derate above 25℃	2.22	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T_J，T_{STG}	-55～+150	℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300	℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项　　目 Parameter	符　号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏一源击穿电压 Drain-Source Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	200	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBVDSS/ΔTJ	ID=250μA, referenced to 25℃	-	0.22	-	
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V,V_{GS}=0V,T_C=25℃	-	-	1	μA
		V_{DS}=160V,　T_C=125℃	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	V_{DS}=0V,　V_{GS} =30V	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	V_{DS}=0V,　V_{GS} =-30V	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} ,　I_D=250μA	2	-	4	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS} =10V ,　I_D=25A	-	42	50	mΩ
正向跨导 Forward Transconductance	g_{fs}	V_{DS} = 40V,　I_D=25A （note 4）		27	-	S
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	V_{DS}=25V, V_{GS} =0V, f=1.0MHz	-	3250	4225	pF
输出电容 Output capacitance	C_{oss}		-	672	863	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	70	91	pF

电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	t_d(on)	V_{DD}=100V,I_D=50A,R_G=25Ω	-	82	112	ns
上升时间 Turn-On rise time	t_r	V_{GS} =10V	-	501	655	ns
延迟时间 Turn-Off delay time	t_d(off)	（note 4，5）	-	237	309	ns
下降时间 Turn-Off Fall time	t_f		-	202	263	ns
栅极电荷总量 Total Gate Charge	Q_g	V_{DS} =160V ,	-	90	110	nC
栅－源电荷 Gate-Source charge	Q_{gs}	I_D=50A	-	26	-	nC
栅－漏电荷 Gate-Drain charge	Q_{gd}	V_{GS} =10V （note 4，5）	-	33	-	nC
漏－源二极管特性及最大额定值 **Drain-Source Diode Characteristics and Maximum Ratings**						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	50	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	200	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=50A	-	-	1.5	V
反向恢复时间 Reverse recovery time	t_{rr}	V_{GS}=0V, I_S=50A	-	175	-	ns
反向恢复电荷 Reverse recovery charge	Q_{rr}	dI_F/dt=100A/μs (note 4)	-	1.23	-	μC

热特性 THERMAL CHARACTERISTIC

项 目 **Parameter**	符 号 **Symbol**	**最大 Max** JCS50N20WT/ABT	单 位 **Unit**
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.45	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	℃/W

注释：

1：脉冲宽度由最高结温限制

2：L=0.8mH, I_{AS}=50A, V_{DD}=50V, R_G=25 Ω,起始结温 T_J=25℃

3：I_{SD} ≤50A,di/dt ≤300A/μs,VDD≤BV_{DSS},起始结温 T_J=25℃

4：脉冲测试：脉冲宽度≤300μs,占空比≤2%

5：基本与工作温度无关

Notes:

1：Pulse width limited by maximum junction temperature

2：L=0.8mH, I_{AS}=50A V_{DD}=50V, R_G=25 Ω,Starting T_J=25℃

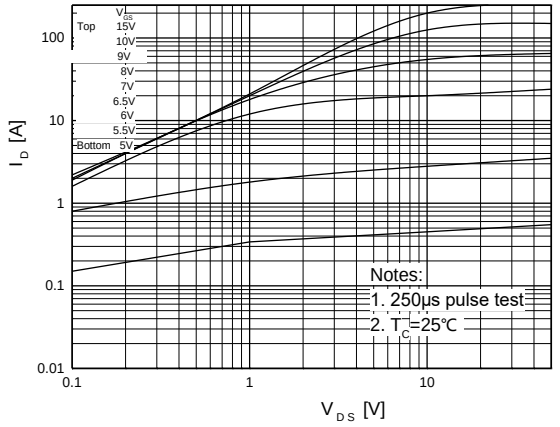
3：I_{SD} ≤50A,di/dt ≤300A/μs,VDD≤BV_{DSS}, Starting T_J=25℃

4：Pulse Test：Pulse Width ≤300μs,Duty Cycle≤2%

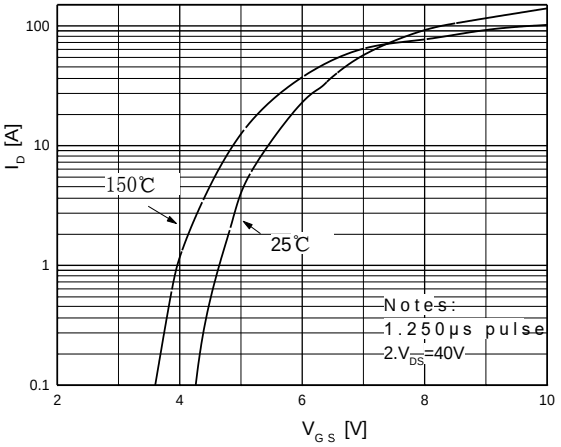
5：Essentially independent of operating temperature

特征曲线　ELECTRICAL CHARACTERISTICS (curves)

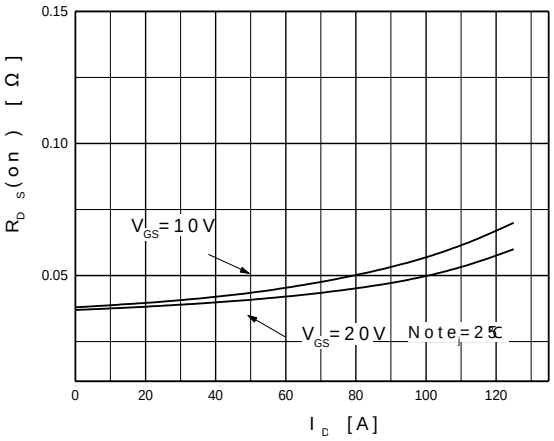
On-Region Characteristics



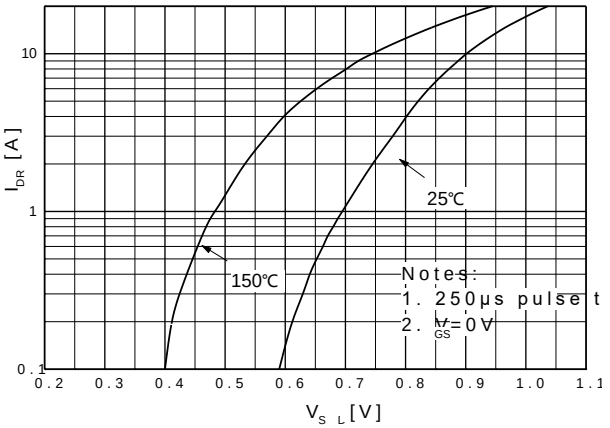
Transfer Characteristics



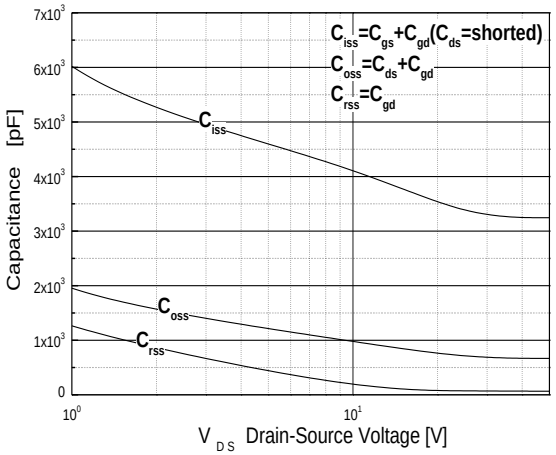
On-Resistance Variation vs. Drain Current and Gate Voltage



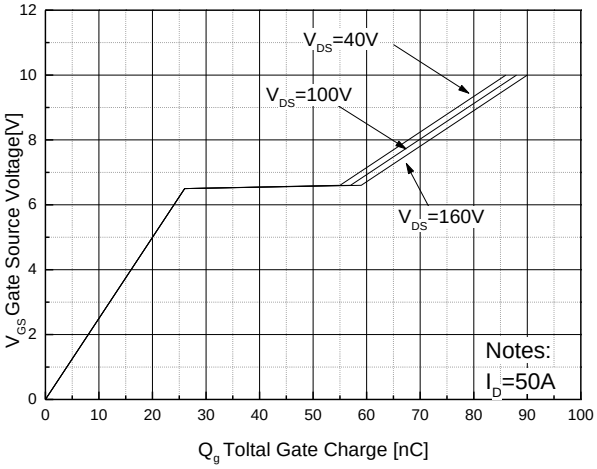
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics

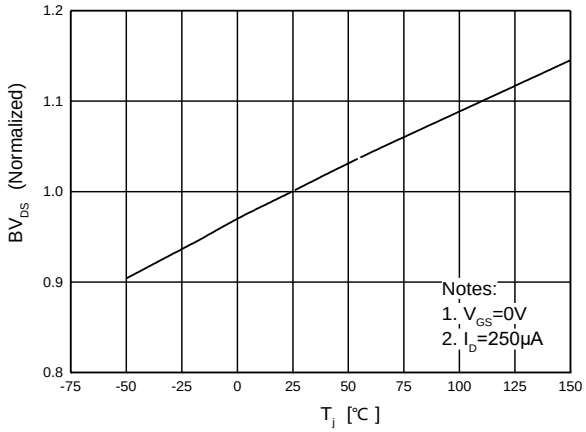


Gate Charge Characteristics

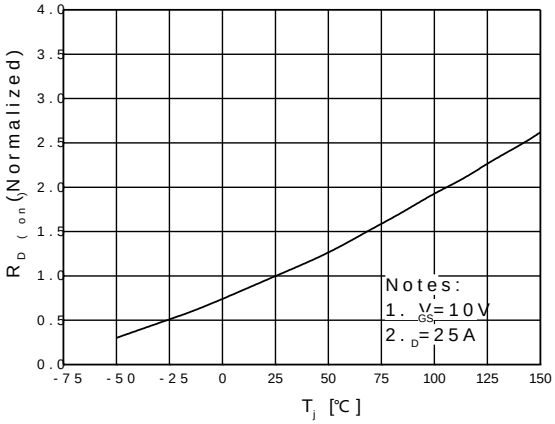


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

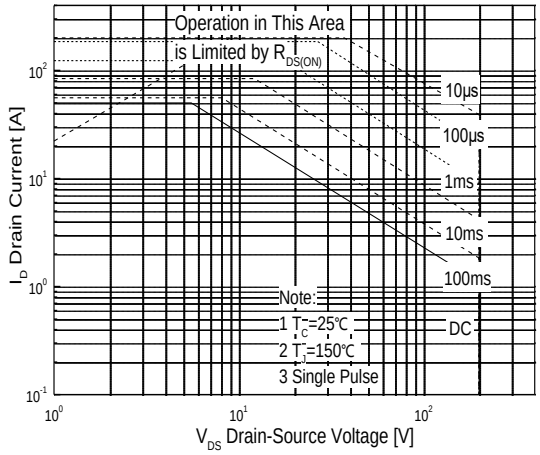
Breakdown Voltage Variation vs. Temperature



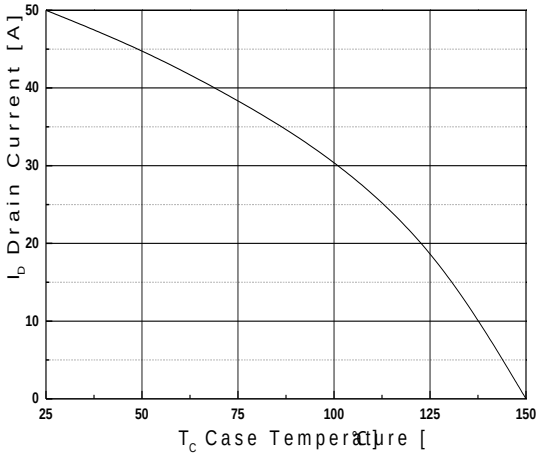
On-Resistance Variation vs. Temperature



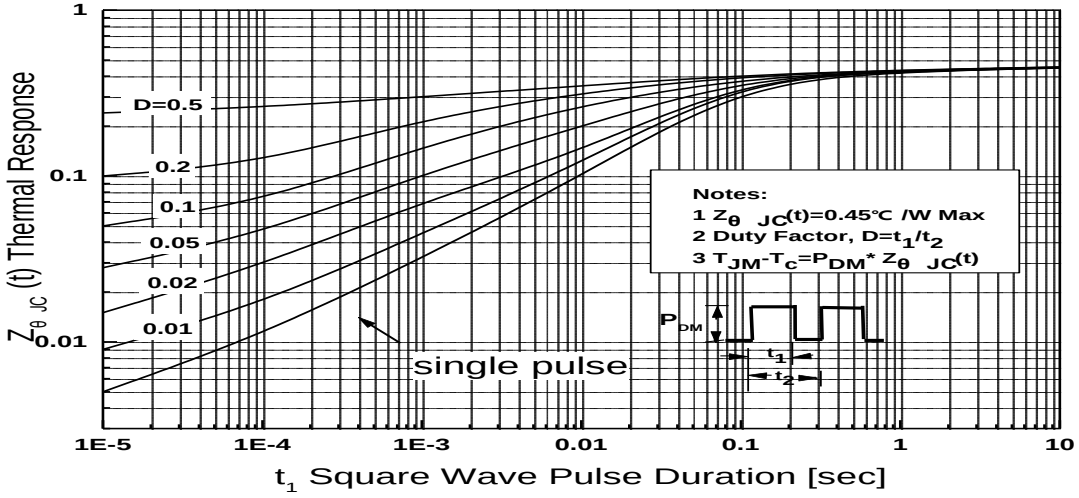
Maximum Safe Operating Area



Maximum Drain Current vs. Case Temperature



Transient Thermal Response Curve

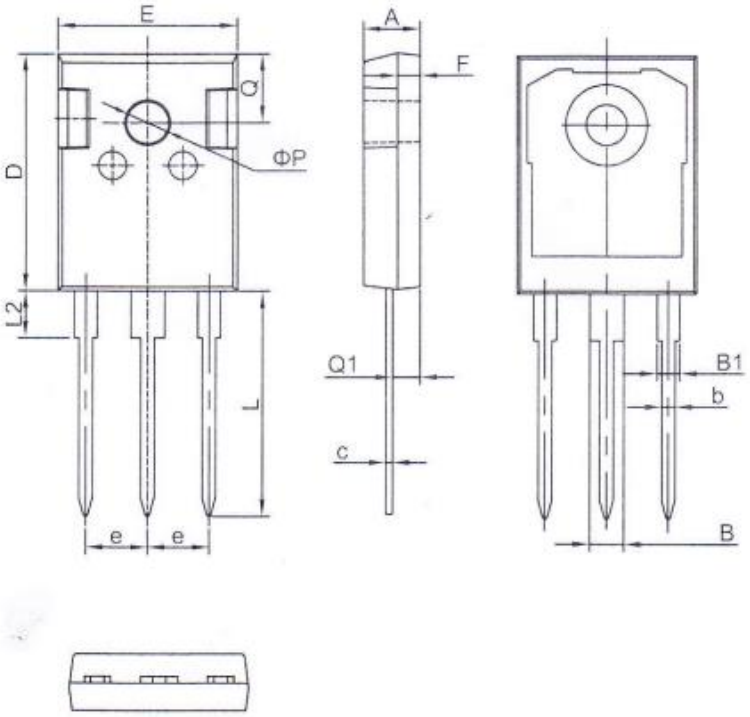


外形尺寸 **PACKAGE MECHANICAL DATA**

TO-247

单位 Unit：mm

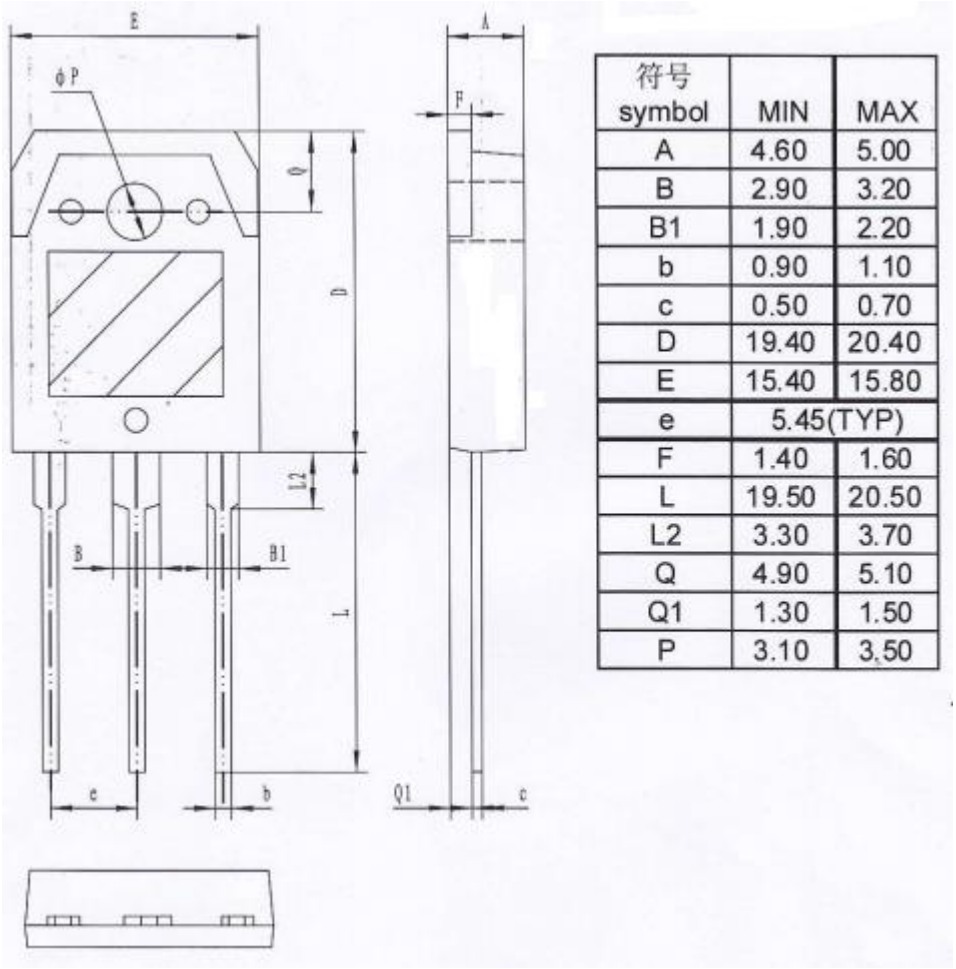
符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70



外形尺寸 **PACKAGE MECHANICAL DATA**

TO-3PB

单位 Unit：mm



符号 symbol	MIN	MAX
A	4.60	5.00
B	2.90	3.20
B1	1.90	2.20
b	0.90	1.10
c	0.50	0.70
D	19.40	20.40
E	15.40	15.80
e	5.45(TYP)	
F	1.40	1.60
L	19.50	20.50
L2	3.30	3.70
Q	4.90	5.10
Q1	1.30	1.50
P	3.10	3.50